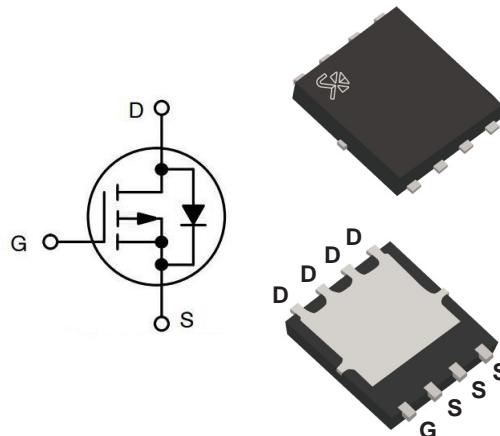


## Feature

- 20V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- $R_{DS(ON)} = 9\text{m}\Omega$ (typ.) @  $V_{GS} = -4.5\text{V}$
- $R_{DS(ON)} = 13\text{m}\Omega$ (typ.) @  $V_{GS} = -2.5\text{V}$
- Reliable and Rugged.

## Applications

- Power Management in Portable Equipment and Battery Powered Systems and other General Application.



**PDFN5060**

### 1. Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	-20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	
$I_D$	Continue Drain Current	-18	A
$I_{DM}$	Pulsed Drain Current	-72	
$I_S$	Diode Continuous Forward Current	-18	A
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient(SOP8)	62.5	$^\circ\text{C}/\text{W}$

### 2. Static Electrical Characteristics ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=-250\mu\text{A}$	-20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$ , $V_{GS}=0\text{V}$			-1	$\mu\text{A}$
		$T_J=85^\circ\text{C}$			-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	-0.5	-0.7	-1	V
$I_{GSS}$	Gate Body Leakage Current	$V_{GS}=\pm 12\text{V}$ , $V_{DS}=0\text{V}$			$\pm 100$	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=-4.5\text{V}$ , $I_D=-1\text{A}$		9	12	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$ , $I_D=-1\text{A}$		13	16	
$V_{SD}$	Diode Forward Voltage	$I_{SD}=-1\text{A}$ , $V_{GS}=0\text{V}$		-0.7	-1.3	V

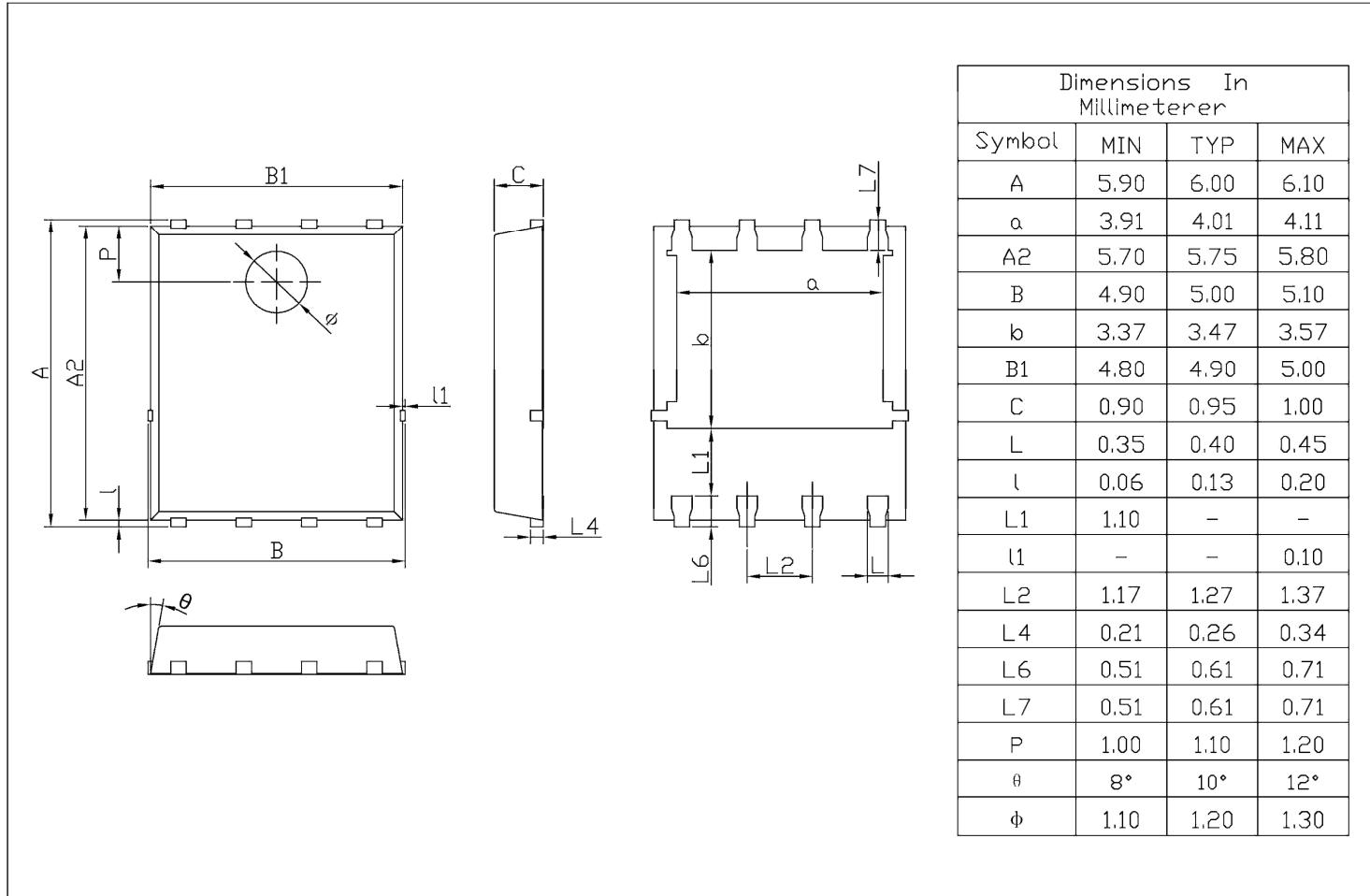
\*Note:

a : Current maybe limit by bonding wire.

b : The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to ambient and depend on package type.

**PDFN5060**

Unit:mm



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)